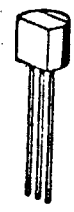


MPS-A93 is PNP silicon planar epitaxial transistor designed for general purpose applications requiring high breakdown voltage, low saturation voltage and low capacitance.

TO-92A



EBC

**ABSOLUTE MAXIMUM RATINGS**

Collector-Emitter Voltage	$V_{CE0}$	200V
Collector-Base Voltage	$V_{CB0}$	200V
Emitter-Base Voltage	$V_{EB0}$	5V
Collector Current	$I_C$	500mA
Total Power Dissipation @ $T_A=25^{\circ}C$ @ $T_C=25^{\circ}C$	$P_{tot}$	625mW 1.5W
Operating Junction & Storage Temperature	$T_j, T_{stg}$	-55 to +150°C

**ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}C$  unless otherwise specified)**

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	$V_{CE0}$	200		V	$I_C=1mA$ $I_B=0$
Collector-Base Breakdown Voltage	$V_{CB0}$	200		V	$I_C=100\mu A$ $I_E=0$
Emitter-Base Breakdown Voltage	$V_{EB0}$	5		V	$I_E=10\mu A$ $I_C=0$
Collector Cutoff Current	$I_{CB0}$		250	nA	$V_{CB}=160V$ $I_E=0$
Emitter Cutoff Current	$I_{EB0}$		100	nA	$V_{EB}=3V$ $I_C=0$
D.C. Current Gain	$H_{FE}$	25 40 30	150		$I_C=1mA$ $V_{CE}=10V$ $I_C=10mA$ $V_{CE}=10V$ $I_C=30mA$ $V_{CE}=10V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.4	V	$I_C=20mA$ $I_B=2mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.9	V	$I_C=20mA$ $I_B=2mA$
Current Gain-Bandwidth Product	$f_T$	50		MHz	$I_C=10mA$ $V_{CE}=20V$ $f=20MHz$
Output Capacitance	$C_{ob}$		8	pF	$V_{CB}=20V$ $I_E=0$ $f=1MHz$



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